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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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HD74HC125/HD74HC126

Quad. Bus Buffer Gates (with 3-state outputs)



ADE-205-439 (Z)
1st. Edition
Sep. 2000

Description

The HD74HC125, HD74HC126 require the 3-state control input C to be taken high to put the output into the high impedance condition, whereas the HD74HC125, HD74HC126 requires the control input to be low to put the output into high impedance.

Features

- High Speed Operation: $t_{pd} = 8 \text{ ns typ}$ ($C_L = 50 \text{ pF}$)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: $1 \mu\text{A max}$
- Low Quiescent Supply Current: $I_{CC} (\text{static}) = 4 \mu\text{A max}$ ($T_a = 25^\circ\text{C}$)

Function Table

Inputs

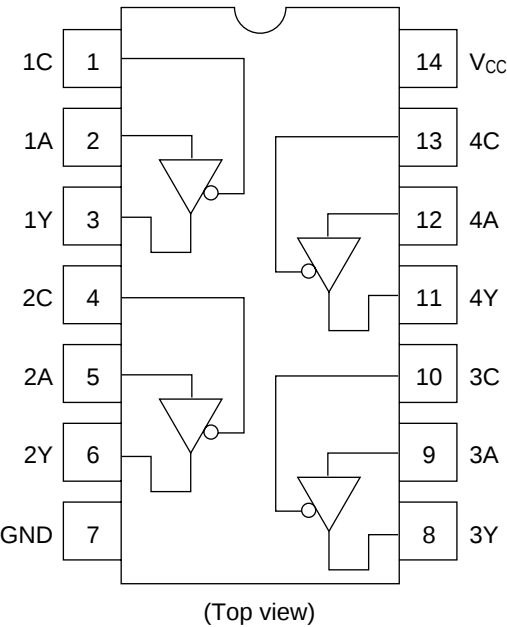
C			Output Y	
HC125	HC126	A	HC125	HC126
H	L	X	Z	Z
L	H	L	L	L
L	H	H	H	H

X : Irrelevant

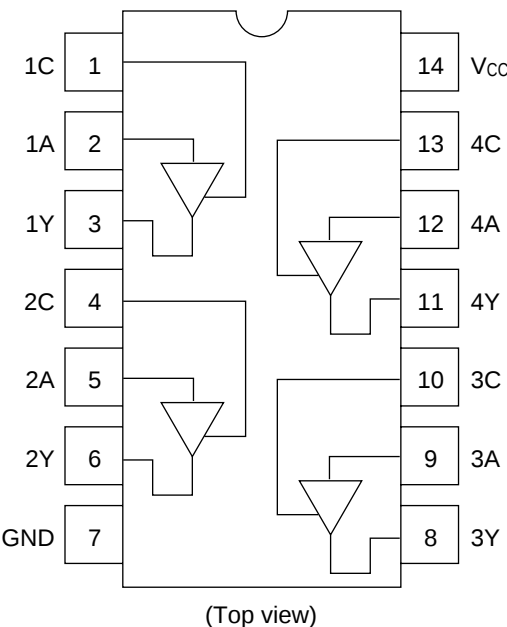
Z : Off (high-impedance) state of a 3-state output.

Pin Arrangement

HD74HC125



HD74HC126



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
Output current	I_{OUT}	± 35	mA
DC current drain per V_{CC} , GND	I_{CC} , I_{GND}	± 75	mA
DC input diode current	I_{IK}	± 20	mA
DC output diode current	I_{OK}	± 20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	Tstg	-65 to +150	°C

DC Characteristics

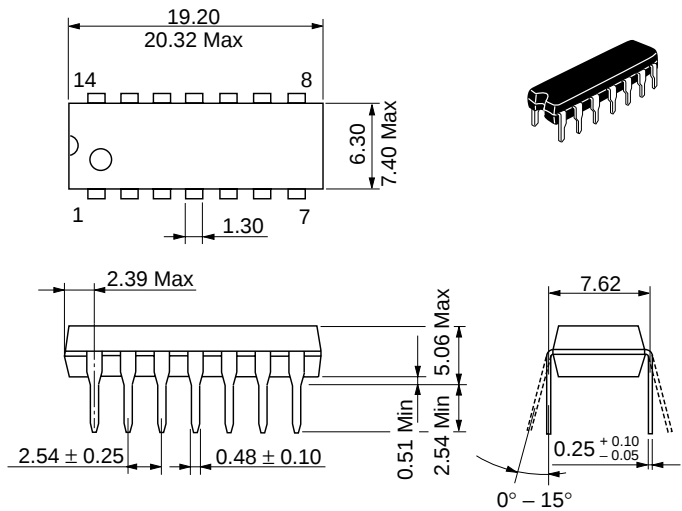
Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V _{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V _{IH} or V _{IL} I _{OH} = -20 µA	
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I _{OH} = -6 mA
		6.0	5.68	—	—	5.63	—			I _{OH} = -7.8 mA
	V _{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V _{IH} or V _{IL} I _{OL} = 20 µA	
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I _{OL} = 6 mA
		6.0	—	—	0.26	—	0.33			I _{OL} = 7.8 mA
Off-state output current	I _{OZ}	6.0	—	—	±0.5	—	±5.0	µA	Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND	
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	µA	Vin = V _{CC} or GND	
Quiescent supply current	I _{CC}	6.0	—	—	4.0	—	40	µA	Vin = V _{CC} or GND, Iout = 0 µA	

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Item	Symbol	$V_{CC} \text{ (V)}$	$T_a = 25^\circ\text{C}$			$T_a = -40 \text{ to } +85^\circ\text{C}$		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Propagation delay time	t_{PLH}	2.0	—	—	100	—	125	ns	
	t_{PHL}	4.5	—	8	20	—	25		
		6.0	—	—	17	—	21		
Output enable time	t_{ZH}	2.0	—	—	150	—	190	ns	
	t_{ZL}	4.5	—	9	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t_{HZ}	2.0	—	—	150	—	190	ns	
	t_{LZ}	4.5	—	14	30	—	38		
		6.0	—	—	26	—	33		
Output rise/fall time	t_{TLH}	2.0	—	—	60	—	75	ns	
	t_{THL}	4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	C_{in}	—	—	5	10	—	10	pF	

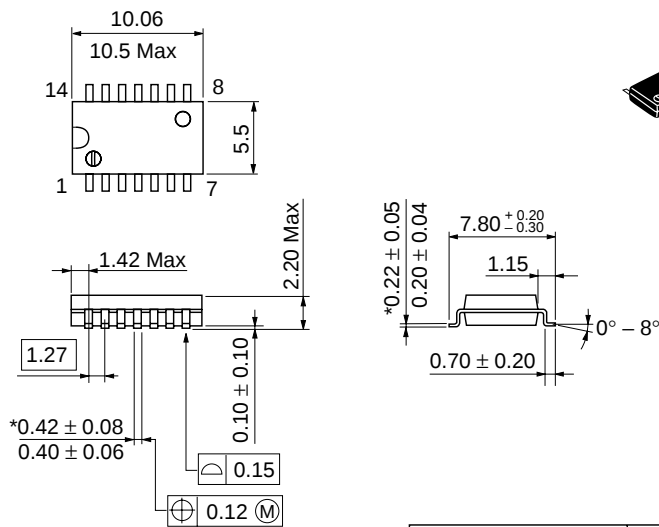
Package Dimensions

Unit: mm



Hitachi Code	DP-14
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.97 g

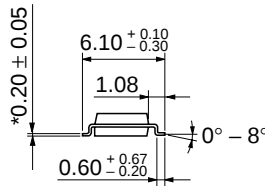
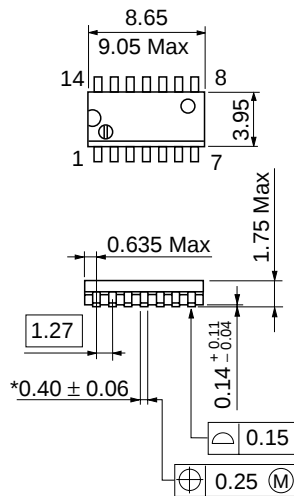
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-14DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.23 g

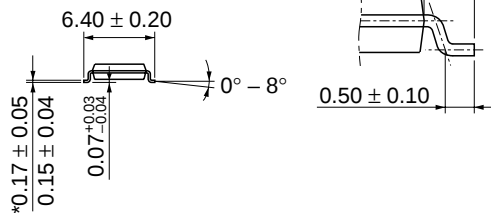
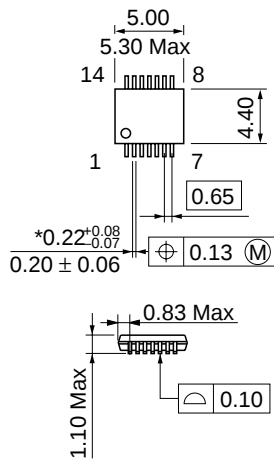
Unit: mm



*Pd plating

Hitachi Code	FP-14DN
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.13 g

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-14D
JEDEC	—
EIAJ	—
Mass (reference value)	0.05 g

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